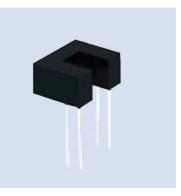


SGM9702

Technical Data Sheet Opto Interrupter SGM9702

Features

- Fast response time
- High analytic
- Peak wavelength $\lambda p=940 nm$
- High sensitivity
- Pb free



Descriptions

The SGM9702 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing. The phototransistor receives radiation from the IR LED only. This is the normal situation. But when an object is in between , phototransistor could not receives the radiation.

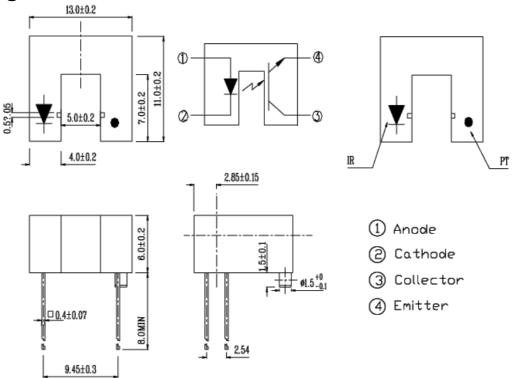
Applications

- Non-contact Switching
- Switch Scanner
- For Direct Board
- Floppy disk driver



2

Package Dimensions



Notes:

- 1. All dimensions are in millimeters
- 2. Tolerances unless dimensions ±0.2mm

Absolute Maximum Datings (Ta=25°C)

3. Lead spacing is measured where the lead emerge from the package

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	75	mW
	Reverse Voltage	V_R	5	V
	Forward Current	$I_{\rm F}$	50	mA
	Peak Forward Current (*1) Pulse width $\leq 100 \mu$ s, Duty cycle=1%	I_{FP}	1	A
Output	Collector Power Dissipation	Pd	75	mW
	Collector Current	I _C	20	mA
	Collector-Emitter Voltage	${ m B}~{ m V}_{ m CEO}$	30	V
	Emitter-Collector Voltage	${ m B}~{ m V}_{ m ECO}$	5	V
Operating	Temperature	Topr	-25~+85	°C
Storage Temperature		Tstg	-40~+85	°C
	ering Temperature (*2) form body for 5 seconds)	Tsol	260	°C

(*1) tw=100 μ sec., T=10 msec. (*2) t=5 Sec

SHENZHEN SHUGUAN ELECTRONIC TECHNOLOGY CO., LTD. V1.0 2010.07.10

_			



3

Electro-Optical Characteristics (1a=25 C)							
Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions
	Forward Voltage	$V_{\rm F}$		1.2	1.5	V	I _F =20mA
	Reverse Current	I_R			10	μA	V _R =5V
Input	Peak Wavelength	λр		940		nm	I _F =20mA
	View Angle	201/2		60		Deg	I _F =20mA
	Dark C urrent	I _{CEO}			100	nA	V _{CE} =20V,Ee=0mW/cm ²
Output	C-E Saturation Voltage	V _{CE} (sat)			0.4	v	I _C =2mA ,Ee=1mW/cm ²
	Collect Current	I _C (ON)	0.5		10	mA	V _{CE} =5V
Transfer	concer current	Ic(OFF)			20	μA	I _F =20mA
Characteristic	Rise time	t _r		15		$\mu \sec$	V _{CE} =5V
	Fall time	t_{f}		15		$\mu \sec$	I _C =1mA
							$R_L=1K\Omega$

Electro-Optical Characteristics (Ta=25°C)

Typical Electrical/Optical/Characteristics Curves for IR

Fig.1 Forward Current vs.

Ambient Temperature

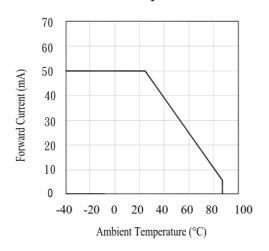
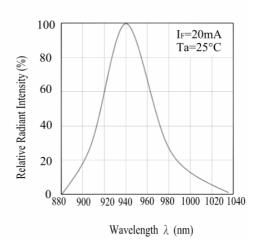
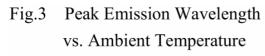
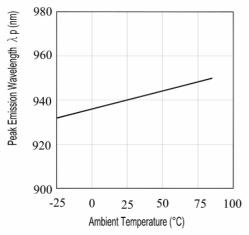


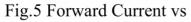
Fig.2 Spectral Distribution











Ambient Temperature(°C)

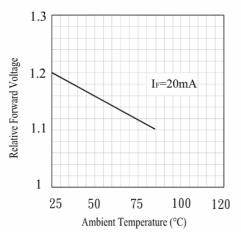


Fig.4 Forward Current

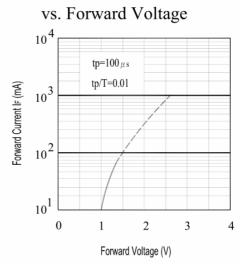
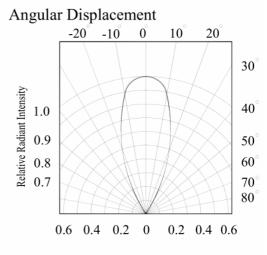


Fig.6 Relative Radiant Intensity vs.



Typical Electrical/Optical/Characteristics Curves for PT

Fig.1Collector Power Dissipation vs.

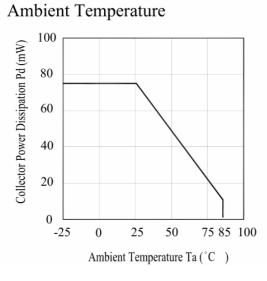
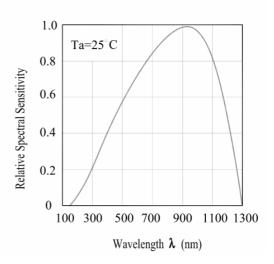
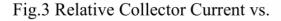


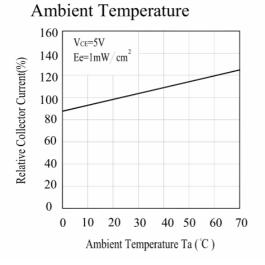
Fig.2 Spectral Sensitivity



SHENZHEN SHUGUAN ELECTRONIC TECHNOLOGY CO., LTD. V1.0 2010.07.10









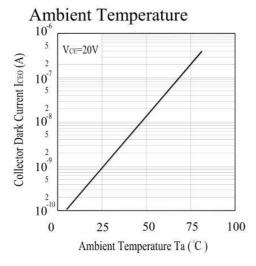


Fig.4 Collector Current vs.

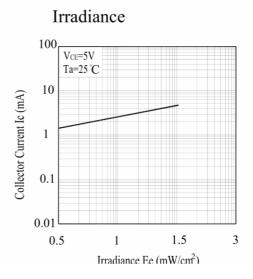
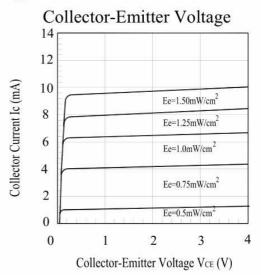


Fig.6 Collector Current vs.



Packing Quantity Specification

1. 100PCS/1Bag

Notes

- 1. Above specification may be changed without notice. SHUGUAN will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. SHUGUAN assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
- 3. These specification sheets include materials protected under copyright of SHUGUAN corporation. Please don't reproduce or cause anyone to reproduce them without SHUGUAN's consent.